

BI-DIRECTIONAL TRIODE THYRISTOR
SILICON PLANAR TYPE

SM2(B, D, G)41

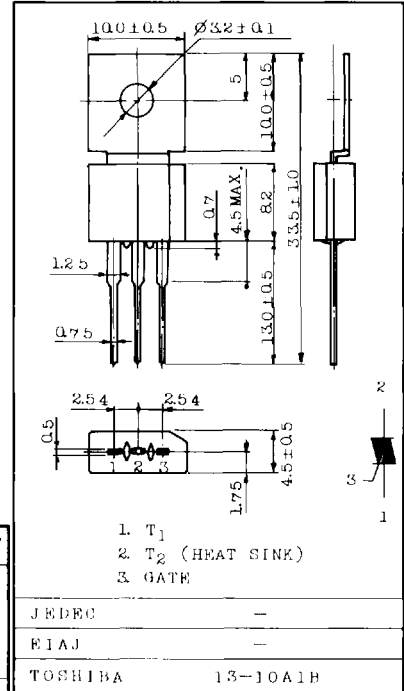
AC POWER CONTROL APPLICATIONS.

- . Repetitive Peak Off-State Voltage : $V_{DRM}=100 \sim 400V$
- . R.M.S On-State Current : $I_T(RMS)=2A$
- . Suitable for Heating Control, Motor Control, Dimmer and Switching Systems.

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage	SM2B41	V_{DRM}	100	V
	SM2D41		200	
	SM2G41		400	
R.M.S On-State Current (Full Sine Waveform $T_c=85^{\circ}C$)		$I_T(RMS)$	2	A
Peak One Cycle Surge On-State Current (Non-Repetitive)		I_{TSM}	12(50Hz)	A
			13(60Hz)	
I^2t Limit Value ($t=1 \sim 10ms$)		I^2t	0.72	A^2s
Peak Gate Power Dissipation		PGM	3	W
Average Gate Power Dissipation		$P_{G(AV)}$	0.3	W
Peak Gate Voltage		V_{GM}	10	V
Peak Gate Current		I_{GM}	1.6	A
Junction Temperature		T_j	-40 ~ 125	$^{\circ}C$
Storage Temperature Range		T_{stg}	-40 ~ 125	$^{\circ}C$

Unit in mm



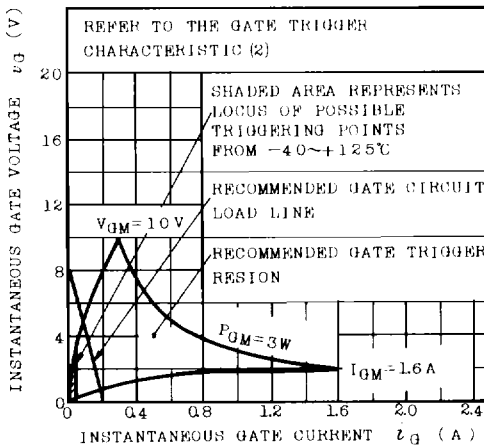
Weight : 1.5g

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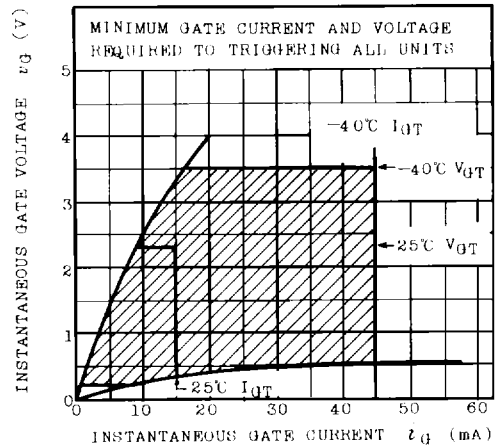
ELECTRICAL CHARACTERISTICS (Ta=25°C)

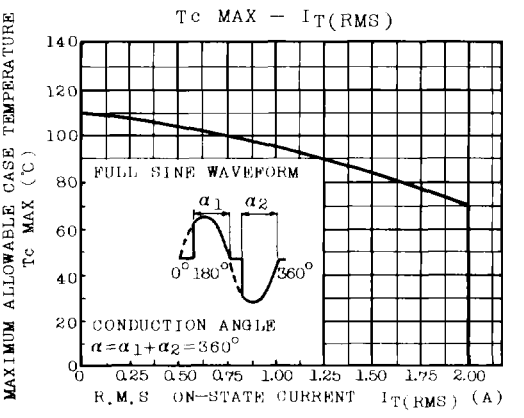
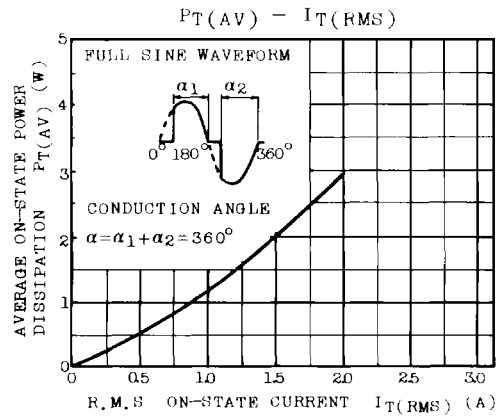
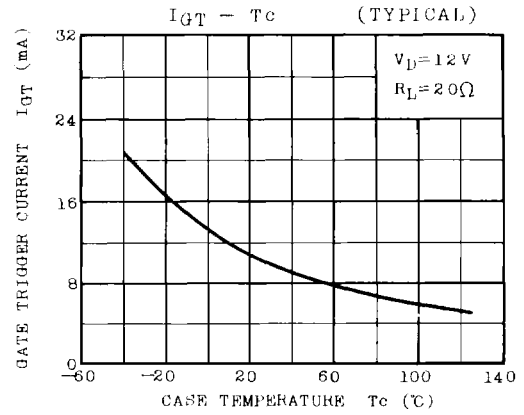
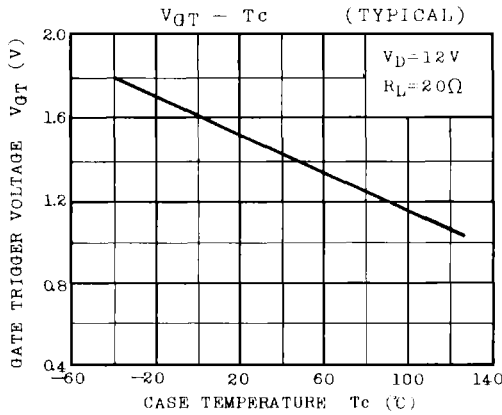
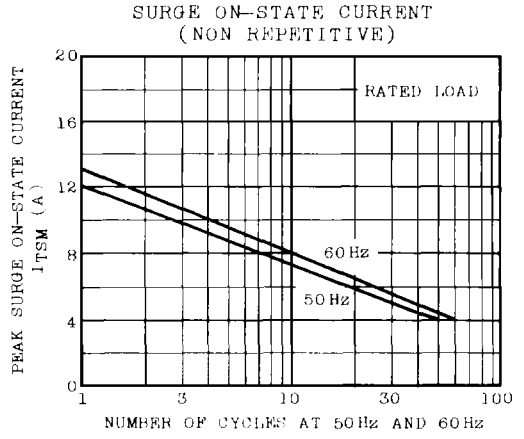
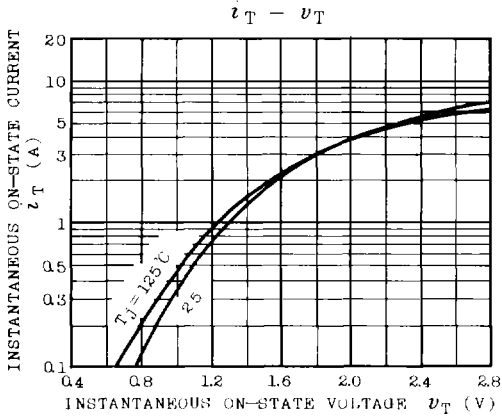
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Repetitive Peak Off-State Current	I_{DRM}	$V_{DRM} = \text{Rated}, T_j = 125^\circ\text{C}$	-	-	100	μA	
Gate Trigger Voltage	I II III IV V_{GT}	$V_D = 12\text{V}$	T2(+), Gate(+)	-	-	2.3	V
			T2(+), Gate(-)	-	-	2.3	
			T2(-), Gate(-)	-	-	2.3	
			T2(-), Gate(+)	-	1.8	-	
Gate Trigger Current	I II III IV I_{GT}	$R_L = 20\Omega$	T2(+), Gate(+)	-	-	15	mA
			T2(+), Gate(-)	-	-	15	
			T2(-), Gate(-)	-	-	15	
			T2(-), Gate(+)	-	15	-	
Peak On-State Voltage	V_{TM}	$I_{TM} = 6\text{A}$	-	-	2.6	V	
Gate Non-Trigger Voltage	V_{GD}	$V_D = \text{Rated}, T_c = 125^\circ\text{C}$	0.2	-	-	V	
Holding Current	I_H	$R_L = 100\Omega$	-	-	25	mA	
Thermal Resistance	$R_{th(j-c)}$	Junction to Case, AC	-	-	12	$^\circ\text{C/W}$	

GATE TRIGGER CHARACTERISTIC (1)



GATE TRIGGER CHARACTERISTIC (2)





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